# Effect of ECR-Ion Milling on Exchange Biasing in NiO/NiFe Bilayers

D. G. Hwang, S. S. Lee, K. H. Lee, K. B. Lee, D. H. Park and H. S. Lee

Department of Physics, Sangji University, Wonju 220-702, Korea

(Received 20 December 1999)

We have investigated the effects of Ar and  $O_2$ -ion milling on the exchange coupling field  $(H_{ex})$  and coercive field  $(H_c)$  at the interfaces between substrates and NiO/NiFe films, to understand the exchange biasing mechanism. The  $O_2$ -ion milling was successfully performed by means of the electron cyclotron resonance (ECR) process. We found that the local roughness gradient of the NiO surface increased by  $O_2$ -ion milling. The ratio of  $H_{ex}/H_c$  increased from 0.87 to 1.77, whereas  $H_c$  decreased by almost a half as a results of the ion milling. The decrease in  $H_c$  could be interpreted as due to the refinement of magnetic domain size, which arose from the increase of the local roughness gradient of the NiO surface. The decrease in low  $H_c$  and increase in  $H_{ex}$  in NiO spin valves by ECR-ion milling are in the right direction for use in magnetoresistance (MR) heads.

#### 1. Introduction

One of the interesting problems in NiO-based spin-valves is the effect of the interfacial topology on exchange biasing and coercivity. Recently, it has been reported that roughness and grain size are important for the control of exchange biasing. The exchange coupling field ( $H_{ex}$ ) is known to depend mainly on the degree of interfacial roughness rather than on crystallographic texture [1-3]. A few groups reported that  $H_{ex}$  increased with increasing interfacial roughness in NiFe/CoO(111) [4]. On the other hand, it was reported that the grain-size of NiO, rather than the roughness, might be more important to control  $H_{ex}$  [5]. Despite extensive work, many questions remain regarding the role of interface structure.

In our previous work, values of  $H_{ex}$  and  $H_c$  in NiO spinvalves were attributed to the local gradient of surface features rather than rms roughness and crystal texture [6]. In this work, we report the effects of Ar and O<sub>2</sub>-ion milling of the interfaces between substrates and NiO/NiFe bilayers, to get a better understanding of the influence of local roughness gradient on  $H_{ex}$  and  $H_c$ .

### 2. Experimental

The Ar and  $O_2$  ion milling process was performed using ECR milling of the substrate/NiO interface, where Corning glass 7059 and MgO (100) were used as substrates. The ion milling conditions were: acceleration voltage 800 V, beam current 5 mA, milling time 30 minutes. Both  $O_2$  and Ar gas pressures were 1 mTorr. The incident angle of the ion beam was  $45^{\circ}$  to the plane of the glass substrates. Since the surface morphology of a single crystal varies with incidence

angle, the incident beam was varied in both the incident angle  $\theta$  and the azimuthal angle  $\varphi$  (measured from the [001] direction), as follows i)  $\theta$ ,  $\varphi = 0^{\circ}$ , ii)  $\theta$ ,  $\varphi = 45^{\circ}$ , and iii)  $\theta = 45^{\circ}$ ,  $\varphi = 0^{\circ}$ , to obtain various surface morphologies of the MgO (100) substrates.

The NiO(450 Å)/NiFe(50 Å)/Cu(18 Å)/NiFe(60 Å) spin valves and NiO(350 Å)/NiFe(50 Å) bilayers were deposited by means of rf and dc magnetron sputtering at rates of about  $6\sim10$  Å/min and 1.5 Å/sec in an Ar pressure of 1.5 mTorr, respectively. A uniaxial magnetic field of 320 Oe was applied during deposition. The  $H_{ex}$  and  $H_c$  values of the NiO/NiFe bilayers were obtained from magnetoresistance (MR) and M-H curves. The surface morphologies of the NiO films were examined using an atomic force microscope (AFM).

#### 3. Results and Discussion

Figure 1 shows the surface morphologies of glass/NiO(350 Å) and the M-H curves of glass/NiO(350 Å)/NiFe(50 Å) with and without ECR Ar and O<sub>2</sub>-ion milling of the glass/NiO interface. The values of  $H_{\rm ex}$  and  $H_{\rm c}$  of the bilayers without ion milling were 117 Oe and 135 Oe, respectively. After Ar-ion milling, both  $H_{\rm ex}$  and  $H_{\rm c}$  decrease, to 100 Oe and 65 Oe, respectively. In the case of O<sub>2</sub>-ion milling,  $H_{\rm ex}$  increases to 129 Oe and  $H_{\rm c}$  decreases to 73 Oe. The ratio  $H_{\rm ex}/H_{\rm c}$  increases from 0.87 to 1.77 by O<sub>2</sub> ion milling. The rms surface roughness of the glass substrates after Ar and O<sub>2</sub> ion milling increased slightly from 0.98 Å before milling to 2.0 Å and 2.6 Å after milling. These results indicate that the ion milling caused interfacial roughness to increase, and enhanced the  $H_{\rm ex}/H_{\rm c}$  ratio in the NiO/NiFe bilayers.

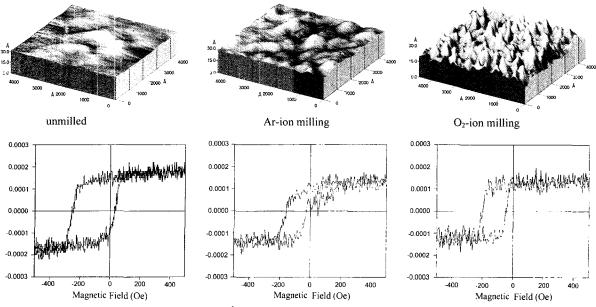


Fig. 1. The surface morphologies of glass/NiO(350 Å) and M-H curves of glass/NiO(350 Å)/NiFe(50 Å) with and without ECR  $O_2$  and Ar ion milling.

The local roughness gradient ( $R_{grad}$ ), defined as the ratio of average wavelength to peak-to-valley height of clusters in the AFM image, was introduced in order to explain the dependence of exchange biasing on roughness. The quantity  $R_{grad}$  was called the slope of roughness  $R_s$  in our earlier works [6, 7]. Rms roughness ( $R_{rms}$ ) does not specify the local gradient of a cluster, because  $R_{rms}$  is calculated from the heights of an individual AFM image. The  $R_{grad}$  values of two surfaces can be different, even if their  $R_{rms}$  values are identical. The values of  $H_{ex}$  and  $H_c$  in NiO spin valves are attributed to  $R_{grad}$  rather than to  $R_{rms}$ , because the high gradient could both increase the magnetostatic energy and decrease the antiferromagnetic domain size.

The  $R_{grad}$  of NiO film surfaces increases by a factor of 10, from 1/200 to 1/20, by O<sub>2</sub>-gas ion milling, while  $R_{rms}$  increases about 2.6 times, as shown in Table 1. The change in  $H_{\rm ex}$  by ion milling is not very significant, but that in  $H_{\rm c}$  is appreciable. Such changes may be due to the reduction of magnetic domain size in the NiFe film. The high gradient

increases the local demagnetization field, and the magnetic domain size is reduced in order to decrease magnetostatic energy. The reduced domain size aids in easy displacement of domain walls [7].

Table 1 shows the ECR ion milling conditions, the rms roughness, the local roughness gradient, and  $H_{ex}$  and  $H_c$ , in NiO/NiFe bilayers deposited on Corning glass 7059 and MgO(100). We expected that the MgO(100) substrates milled with various incident angles of the O<sub>2</sub>-gas ion beam, would have different anisotropic surfaces. However, only surface roughness was changed. NiO films deposited on milled MgO(100) have a larger roughness than those on glass substrates. For a specimen without ion milling, the  $H_{ex}$  and  $H_c$  values are 93 Oe and 116 Oe, respectively. Both these values are lower than those on glass,  $[H_{ex}=117\ \text{Oe}]$  and  $H_c=135\ \text{Oe}]$ , but the  $H_{ex}/H_c$  ratio is almost the same, about 0.8. The  $H_{ex}/H_c$  ratio for the perpendicular incident beam  $(\theta=0^{\circ}, \varphi=0^{\circ})$  is slightly smaller (0.74) than that for the specimen without ion milling (0.8), and that for the

Table 1. Effects of ion milling of substrates on roughness and magnetic properties

	· ·	C	0 1 1			
Substrate	Milling conditions	rms roughness	local roughness gradient	$H_{\mathrm{ex}}$	$H_{\rm c}$	$H_{\rm ex}/H_{\rm c}$
Corning 7059	none	0.98 Å	1/200	117 Oe	135 Oe	0.87
	Ar-ion milling	2.0 Å	1/80	100 Oe	65 Oe	1.54
	O <sub>2</sub> -ion milling	2.6 Å	1/20	129 Oe	73 Oe	1.77
MgO	none	8.3 Å	1/10	93 Oe	116 Oe	0.80
(100)	$\theta = 0^{\circ}, \ \varphi = 0^{\circ}$ O <sub>2</sub> -ion milling	10 Å	1/6	100 Oe	135 Oe	0.74
	$\theta$ =45°, $\varphi$ =0° O <sub>2</sub> -ion milling	11 Å	1/3	99 Oe	91 Oe	1.09
	$\theta$ =45°, $\varphi$ =45° O <sub>2</sub> -ion milling	13 Å	1/4	85 Oe	77 Oe	1.10

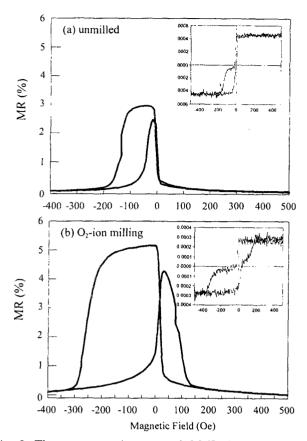


Fig. 2. The magnetoresistance and M-H (inset) curves of glass/NiO(450 Å)/NiFe(50 Å)/Cu(18 Å)/NiFe(60 Å) spin valves (a) with and (b) without  $O_2$  ion milling, where the deposition rate of NiO is 10 Å/min.

inclined ( $\theta$ =45°,  $\varphi$ =0°) or rotated ( $\theta$ = $\varphi$ =45°) ion milling beam increases to about 1.1. Therefore, ECR-ion milling of both glass and MgO substrates enhances the  $H_{ev}/H_{e}$  ratio.

Figure 2 shows the MR and M-H curves of glass/NiO(450 Å)/NiFe(50 Å)/Cu(18 Å)/NiFe(60 Å) spin valves with and without  $O_2$ -ion milling, where the deposition rate of NiO is 10 Å/min. From the M-H curve, it is seen that ion milling increases  $H_{ex}$  and  $H_c$ . The MR curve of the unmilled spin valves has an MR ratio of 3%. However, by  $O_2$ -ion milling, the MR ratio increases to 5.2%. The difference between the  $H_{ex}$  and  $H_c$  of the spin valves and the bilayers is caused by the different deposition rate and thick-

ness of the NiO layer, and the exchange coupling between the pinned NiFe and free NiFe. These results show that the MR ratio and exchange biasing field are improved by the  $O_2$ -ion milling process. Large MR ratio and high exchange biasing in NiO spin-valves are advantageous for application in magnetoresistive read heads.

### 4. Conclusions

The effects of ECR-ion milling of the substrate on exchange biasing and coercivity in NiO/NiFe bilayers deposited on glass and on MgO(100) have been investigated. The ECR-oxygen ion milling process improves the  $H_{ex}/H_c$  ratio. Especially for glass substrates,  $H_c$  decreased by one-half, and the MR ratio in the spin-valves doubled, as a results of milling. Therefore the oxygen ion milling process is a useful method to improve MR and the  $H_{ex}/H_c$  ratio.

## Acknowledgement

The authors would like to acknowledge gratefully that the present work was supported by the Nano Structure Technology Project of MOST.

#### References

- [1] J. X. Shen and M. T. Kief, J. Appl. Phys., 79, 5008 (1996).
- [2] J. Nogues, D. Lederman, T. J. Moran, Ivan K. Schuller, and K. V. Rao, Appl. Phys. Lett., 68, 3186 (1996); W. F. Egelhoff, Jr., P. J. Chen, C. J. Powell, M. D. Stiles, and R. D. McMichael, J. Appl. Phys., 79, 2491 (1996).
- [3] S. Soeya, M. Fuyama, S. Tadokoro, and T. Imagawa, J. Appl. Phys., 79, 1604 (1995).
- [4] T. J. Moran, J. M. Gallego, and Ivan K. Schuller, J. Appl. Phys., 78, 1887 (1995).
- [5] C. H. Lai, T. C. Anthony, E. Iwamura, and R. L. White. IEEE Trans. Magn., Vol. 32, 3419 (1996).
- [6] D. G. Hwang, S. S. Lee, and C. M. Park, Appl. Phys Lett., 72, No. 17, 2162-2164 (1998); D. G. Hwang, C. M Park, S. S. Lee, J. of Mag. Mag. Mat., 186, 265-276 (1998).
- [7] D. G. Hwang, S. S. Lee, and C. M. Park, J. of Mag. Mag Mat., 198, 39-41 (1999).